

2.6

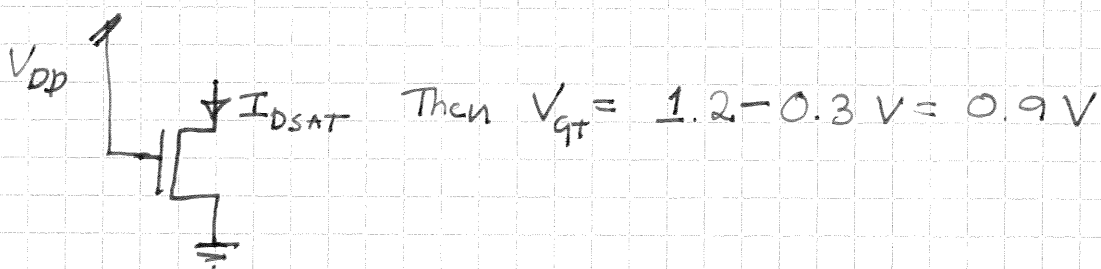
We know $k = 900 \frac{\mu A}{V^2}$

$V_T = 0.30 V$

(a) Calculate the gate voltage overdrive, V_{GT} , if $V_{DD} = 1.2 V$

In the general case $V_{GS} - V_T$ cannot be determined.

Here we assume that transistor is used as a switch and when the transistor is ON $V_G = V_{DD}$



(b) $I_{DSAT} = \frac{k}{2} V_{GT}^2$

so $I_{DSAT} = \frac{900}{2} \left[\frac{\mu A}{V^2} \right] \cdot (0.9)^2 [V^2] = 450 \cdot 0.81 \mu A = 364.5 \mu A$

(c) V_{DSAT} is the ^{drain-source} voltage for which the transistor is at the border between linear region and saturation

region: $V_{DS} \geq V_{GS} - V_T \Rightarrow V_{DSAT} = V_{GS} - V_T$
saturation requirement

So $V_{DSAT} = 0.9 V$ in our case

2.7 The quadratic current equation:

$$I_{Ds} = \frac{k}{2} \frac{W}{L} (V_{gs} - V_T)^2$$

The subthreshold current equation:

$$I_{Ds} = I_{OFF} e^{\frac{V_{gs}}{n \cdot V_{Th}}}$$

At V_{ON} the two currents are equal:

$$(1) \quad I_{OFF} \cdot e^{\frac{V_{ON}}{n \cdot V_{Th}}} = \frac{k}{2} \frac{W}{L} (V_{ON} - V_T)^2$$

And the derivatives w.r.t V_{ON} are also equal

$$(2) \quad \frac{1}{n \cdot V_{Th}} \cdot I_{OFF} e^{\frac{V_{ON}}{n \cdot V_{Th}}} = k \frac{W}{L} (V_{ON} - V_T)$$

Use (1) in (2):

$$\frac{1}{n \cdot V_{Th}} \cdot \frac{k}{2} \frac{W}{L} (V_{ON} - V_T)^2 = \frac{k}{2} \frac{W}{L} (V_{ON} - V_T)$$

$$\Rightarrow V_{ON} - V_T = 2 \cdot n \cdot V_{Th}$$

$$\boxed{V_{ON} = V_T + 2n \cdot V_{Th}}$$